

C1 (ii) subjecting at least a part of a back of the semiconductor element to processing, wherein the processing applies a stress to the semiconductor element, causing at least a part of the semiconductor element to deform when removed from the board, wherein the semiconductor element operates normally only when the semiconductor device is maintained in a level position.

8. (Three Times Amended) The method of manufacturing a semiconductor device as defined in claim 7,

wherein the step (ii) is specified to be carried out by at least one technique selected from a group consisting of scraping by means of dicing, sand blast, and sandpaper and treatment by means of laser beam projection.

9. (Three Times Amended) The method of manufacturing a semiconductor device as defined in claim 7, wherein the step (ii) results in the semiconductor element having a thickness of 50 μm or less where the semiconductor element is processed.

C2 22. (Twice Amended) A method of manufacturing a semiconductor device, comprising the steps of:

(a) securing a semiconductor element having an integrated circuit to a board so that the semiconductor element is maintained in a level position;

(b) subjecting at least a part of a back of the semiconductor element to processing, wherein the processing applies a stress to the semiconductor element, causing at least a part of the semiconductor element to deform when removed from the board,

wherein the step (b) is specified to be carried out by at least one technique selected from a group consisting of scraping by

Docket No.: 1248-0538P
App. No.: 09/820,671

02 means of dicing, sand blast, and sandpaper and treatment by means
of laser beam projection.
